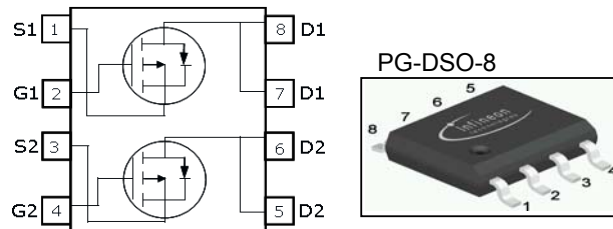


**OptiMOS® P-Power-Transistor**
**Features**

- dual P-Channel in SO8
- Qualified according JEDEC for target applications
- 150°C operating temperature
- Super Logic Level (2.5V rated)
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21


**Product Summary**

$V_{DS}$		-20	V
$R_{DS(on),max}$	$V_{GS}=4.5\text{ V}$	45.0	mΩ
	$V_{GS}=2.5\text{ V}$	70.0	
$I_D$		-5.7	A



Type	Package	Marking	Lead free	Halogen free	Packing
BSO207P H	PG-DSO-8	207P	Yes	Yes	dry

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value		Unit
			10 secs	steady state	
Continuous drain current <sup>1)</sup>	$I_D$	$V_{GS}=4.5\text{ V}, T_A=25\text{ °C}$	-5.7	-5.0	A
		$V_{GS}=4.5\text{ V}, T_A=70\text{ °C}$	-4.6	-4.0	
		$V_{GS}=2.5\text{ V}, T_A=25\text{ °C}$	-4.5	-4.0	
		$V_{GS}=2.5\text{ V}, T_A=70\text{ °C}$	-3.6	-3.2	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_A=25\text{ °C}$	-22.8		
Avalanche energy, single pulse	$E_{AS}$	$I_D=-5.7\text{ A}, R_{GS}=25\text{ Ω}$	44		mJ
Gate source voltage	$V_{GS}$		±12		V
Power dissipation <sup>1)</sup>	$P_{tot}$	$T_A=25\text{ °C}$	2	1.6	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 150		°C
ESD class		JESD22-A114 HBM	1A < 500V		
Soldering temperature			260		°C
IEC climatic category; DIN IEC 68-1			55/150/56		

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Thermal characteristics</b>						
Thermal resistance, junction - soldering point	$R_{thJS}$		-	-	35	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	minimal footprint, $t_p \leq 10$ s	-	-	110	
		minimal footprint, steady state	-	-	150	
		6 cm <sup>2</sup> cooling area <sup>1)</sup> , $t_p \leq 10$ s	-	-	62.5	
		6 cm <sup>2</sup> cooling area <sup>1)</sup> , steady state	-	-	80	

**Electrical characteristics**, at  $T_j=25$  °C, unless otherwise specified

**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0$ V, $I_D=-0.25$ mA	-20	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=44$ $\mu$ A	-0.6	-0.9	-1.2	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=-20$ V, $V_{GS}=0$ V, $T_j=25$ °C	-	0.1	1	$\mu$ A
		$V_{DS}=-20$ V, $V_{GS}=0$ V, $T_j=150$ °C	-	10	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=-12$ V, $V_{DS}=0$ V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=2.5$ V, $I_D=-4.5$ A	-	44	70	m $\Omega$
		$V_{GS}=4.5$ V, $I_D=-5.7$ A	-	32	45	
Gate resistance	$R_G$		-	7.7	-	$\Omega$
Transconductance	$g_{fs}$	$ V_{DS}  > 2 I_D  R_{DS(on)max}$ , $I_D=-4.6$ A	10	18	-	S

<sup>1)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu$ m thick) copper area for drain connection. PCB is vertical in still air.

<sup>2)</sup> See figure 3 for more detailed information

<sup>3)</sup> See figure 13 for more detailed information

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=15\text{ V},$ $f=1\text{ MHz}$	-	1100	1650	pF
Output capacitance	$C_{oss}$		-	380	570	
Reverse transfer capacitance	$C_{rss}$		-	310	465	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-10\text{ V},$ $V_{GS}=4.5\text{ V}, I_D=-5.7\text{ A},$ $R_G=1.6\ \Omega$	-	9	14	ns
Rise time	$t_r$		-	22	33	
Turn-off delay time	$t_{d(off)}$		-	33	50	
Fall time	$t_f$		-	35	53	

**Gate Charge Characteristics<sup>4)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=-10\text{ V}, I_D=-5.7\text{ A},$ $V_{GS}=0\text{ to }4.5\text{ V}$	-	-2	-3	nC
Gate charge at threshold	$Q_{g(th)}$		-	-2	-3	
Gate to drain charge	$Q_{gd}$		-	-5	-7	
Switching charge	$Q_{sw}$		-	-5	-7	
Gate charge total	$Q_g$		-	-12	-16	
Gate plateau voltage	$V_{plateau}$		-	-1.7	-2.5	
Output charge	$Q_{oss}$	$V_{DD}=-10\text{ V}, V_{GS}=0\text{ V}$	-	7	9	nC

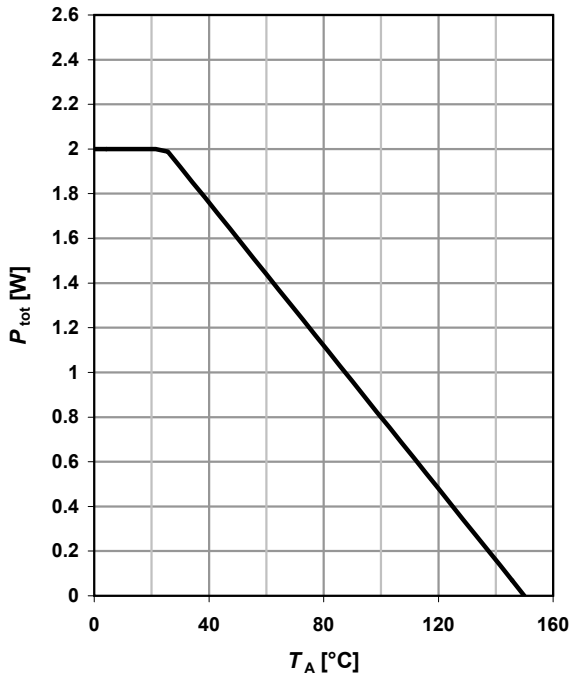
**Reverse Diode**

Diode continuous forward current	$I_S$	$T_A=25\text{ }^\circ\text{C}$	-	-	-2.2	A
Diode pulse current	$I_{S,pulse}$		-	-	-23	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=-5.7\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	-	-1.1	V
Reverse recovery charge	$Q_{rr}$	$V_R=10\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	6.2	-	nC

<sup>4)</sup> See figure 16 for gate charge parameter definition

**1 Power dissipation**

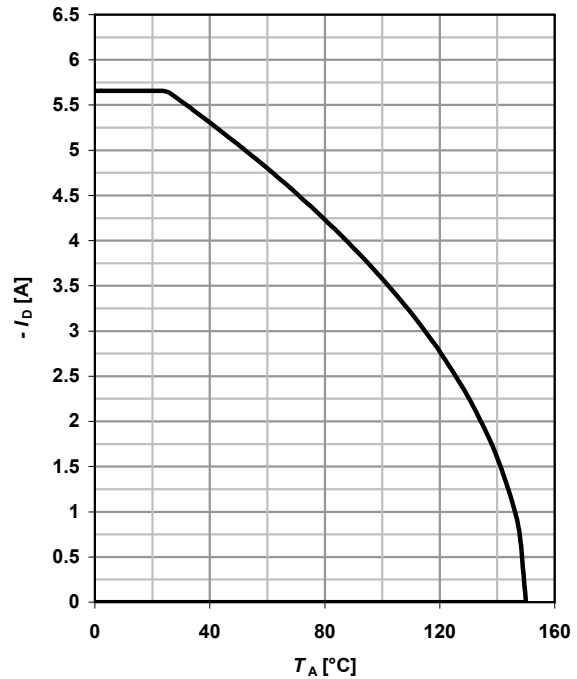
$P_{tot}=f(T_A); t_p \leq 10 \text{ s}$



**2 Drain current**

$I_D=f(T_A); t_p \leq 10 \text{ s}$

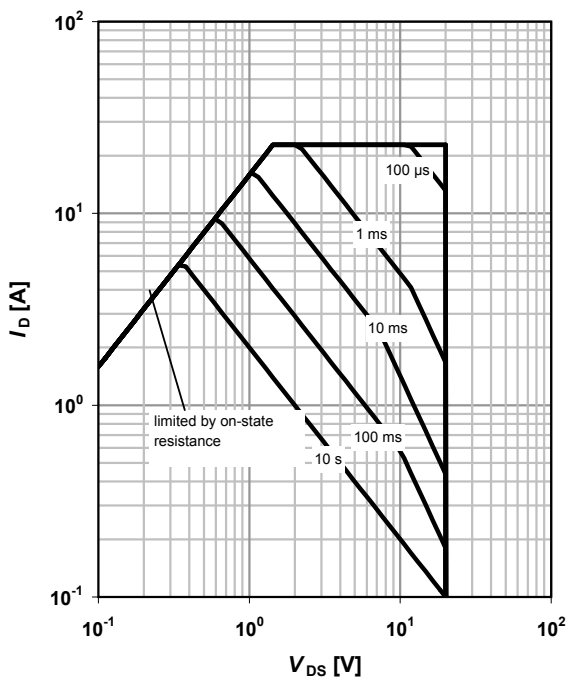
parameter:  $V_{GS} = 4.5 \text{ V}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_A=25 \text{ °C}^2; D=0$

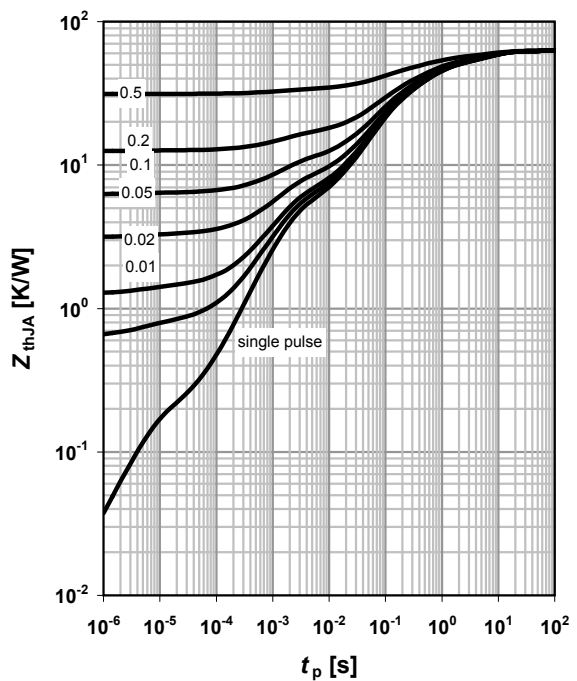
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJA}=f(t_p^2)$

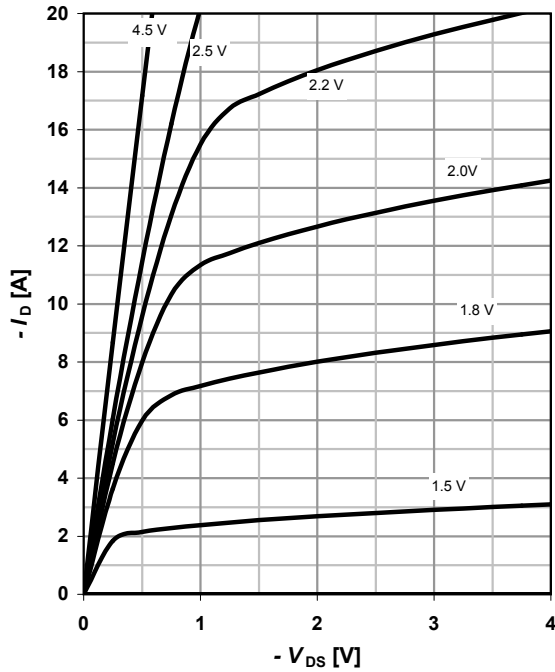
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

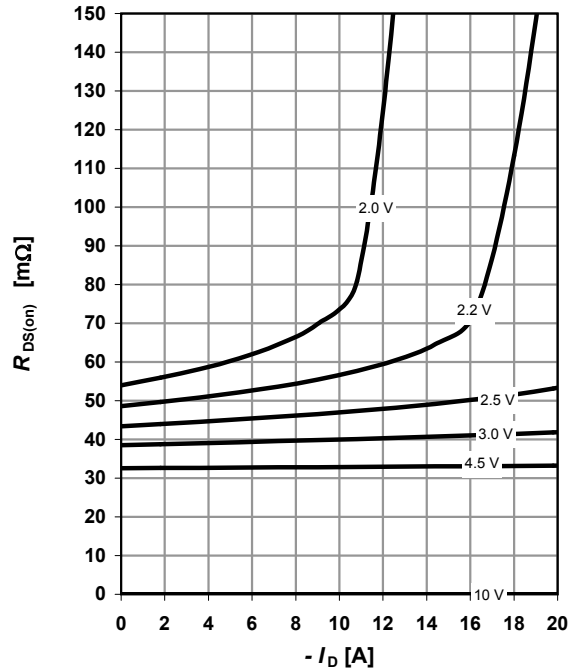
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

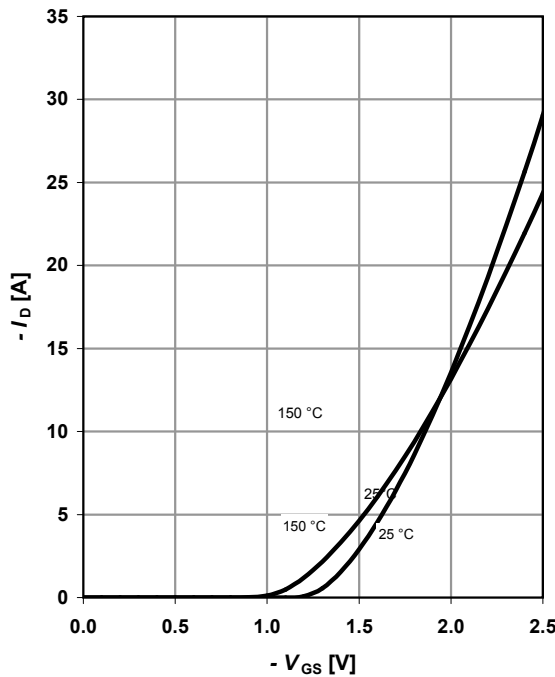
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

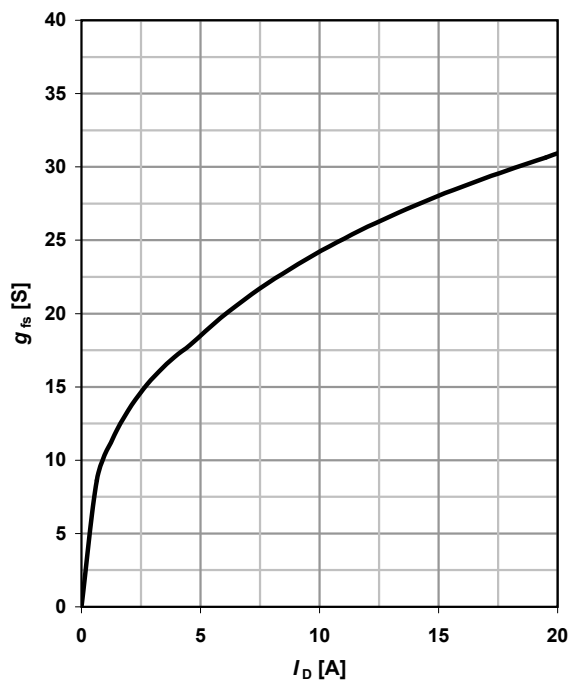
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



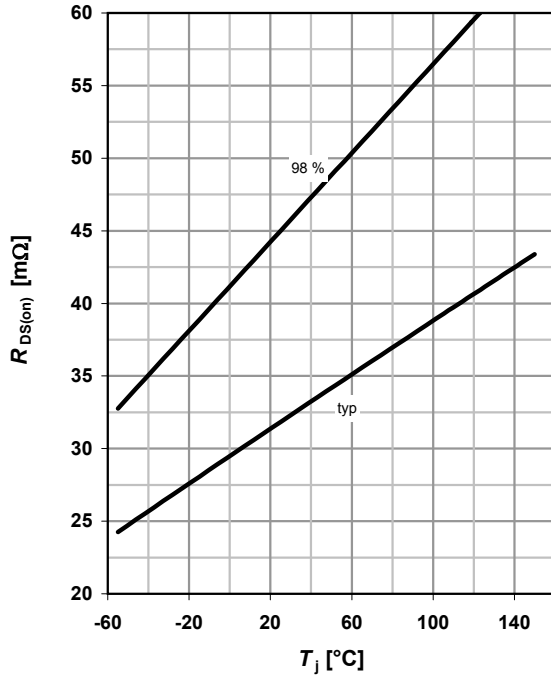
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



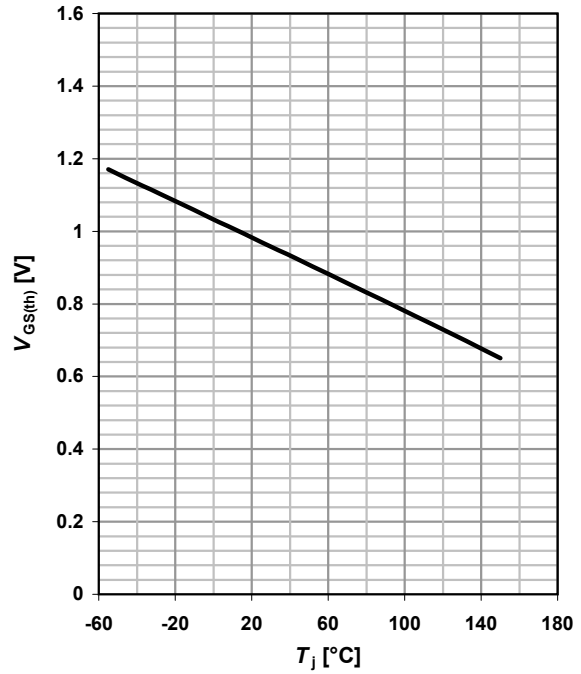
**9 Drain-source on-state resistance**

$R_{DS(on)} = f(T_j); I_D = -5.7 \text{ A}; V_{GS} = -4.5 \text{ V}$



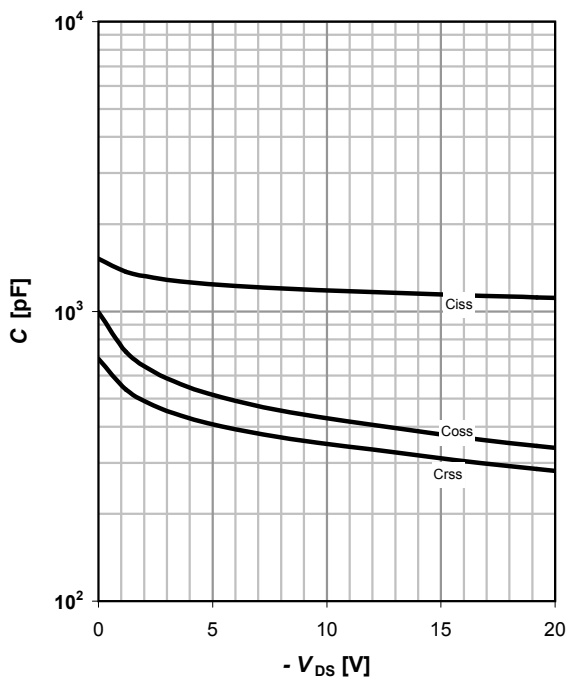
**10 Typ. gate threshold voltage**

$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = -44 \mu\text{A}$



**11 Typ. capacitances**

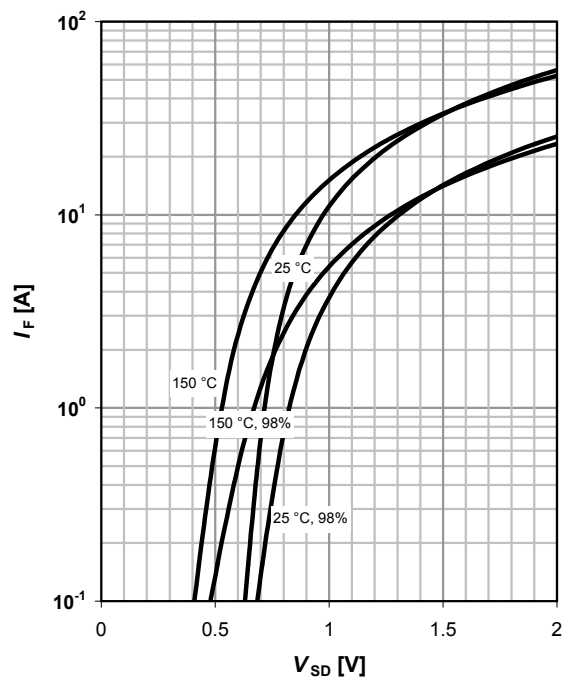
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

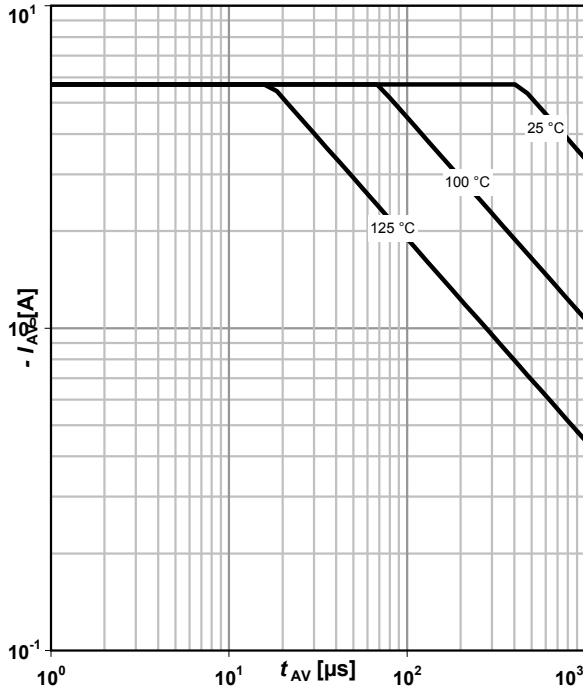
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

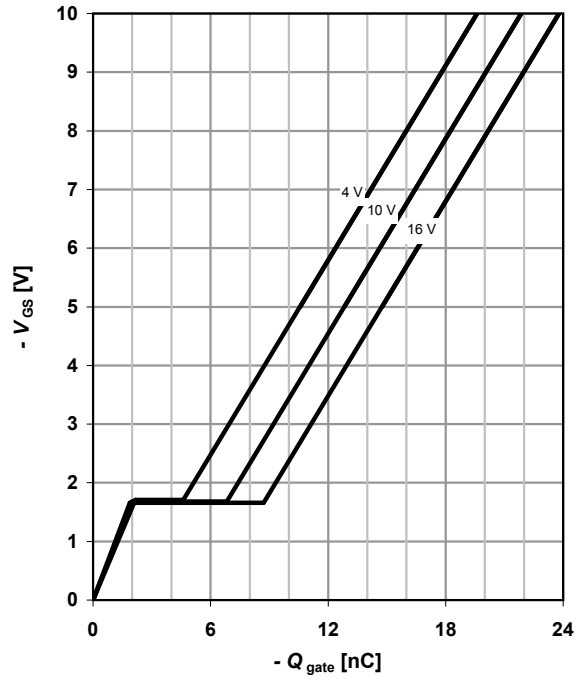
parameter:  $T_{j(start)}$



**14 Typ. gate charge**

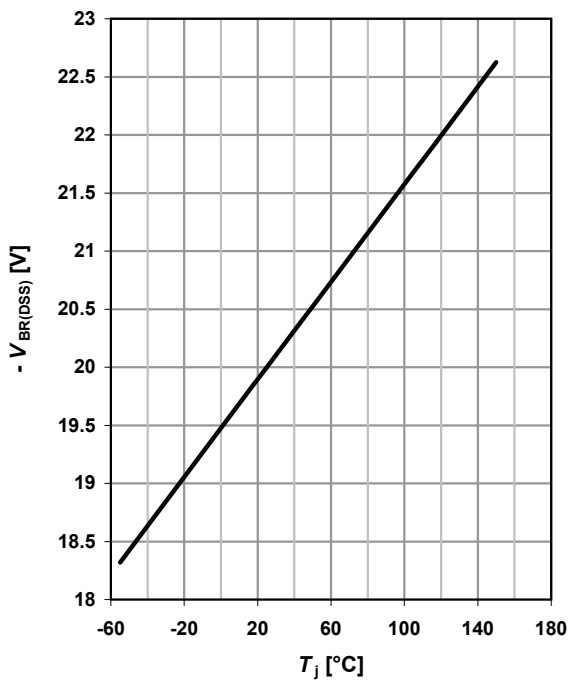
$V_{GS}=f(Q_{gate}); I_D=-5.7 \text{ A pulsed}$

parameter:  $V_{DD}$

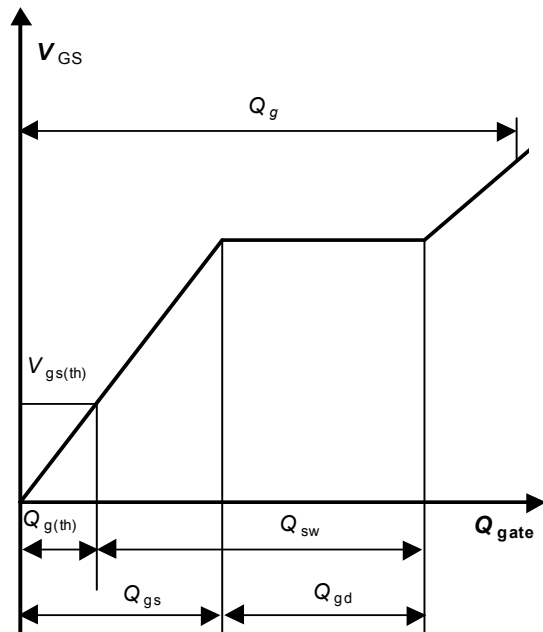


**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=0.25 \text{ mA}$



**16 Gate charge waveforms**



Package Outline

PG-DSO-8: Outline



1) DOES NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.75	-	0.069
A1	0.10	-	0.004	-
A2	1.25	1.65	0.049	0.065
b	0.35	0.51	0.014	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27		0.050	
N	8		8	
L	0.39	0.89	0.015	0.035
h	0.23	0.50	0.009	0.020
theta	0°	8°	0°	8°
theta1	-	19°	-	19°
ccc	0.10		0.004	
ddd	0.25		0.010	
F1	5.59	5.79	0.220	0.228
F2	0.55	0.75	0.022	0.030
F3	1.21	1.41	0.048	0.056

DOCUMENT NO.  
Z8B00003333

SCALE

EUROPEAN PROJECTION

ISSUE DATE  
09.01.2008

REVISION  
02



**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**  
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- Техническая поддержка проекта;
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#### Как с нами связаться

**Телефон:** 8 (812) 309 58 32 (многоканальный)

**Факс:** 8 (812) 320-02-42

**Электронная почта:** [org@eplast1.ru](mailto:org@eplast1.ru)

**Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.